

In the Claims:

Please amend claims 1, 8, 13 and 14. Please cancel claims 15-20. Please add new claims 21-27. The claims are as follows:

1. (Currently Amended) A method, comprising:

- (a) providing a substrate;
- (b) forming a first single-crystal layer on a top surface of said substrate;
- (c) forming a second single-crystal layer on a top surface of said first single-crystal layer;
- (d) forming one or more devices in said second single-crystal layer;
- (e) forming a trench in said second-single crystal layer, said trench surrounding said one or more devices, to form a single-crystal island containing said one or more devices in a region of said second single-crystal layer, said first single-crystal layer exposed in a bottom of said trench; and
- (f) removing said first single-crystal layer in order to separate said single-crystal island from said substrate.

2. (Original) The method of claim 1, wherein step (f) includes selectively removing said first single-crystal layer with respect to said second-single crystal layer.

3. (Original) The method of claim 1, wherein said substrate comprises silicon.

4. (Original) The method of claim 1, wherein said first single-crystal layer comprises Si_xGe_y , Si_xC_y or Si_xAs_y .

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5. (Original) The method of claim 1, wherein said second single-crystal layer comprises silicon.

6. (Original) The method of claim 1, further including:

(g) after step (f) repeating steps (a) through (f) one or more times.

7. (Original) The method of claim 1, further including:

(g) after step (f) mechanical-chemical-polishing said substrate to expose a new top surface of said substrate; and

(h) after step (g) repeating steps (a) through (g) one or more times.

8. (Currently Amended) The method of claim 1, further including:

between steps (e) and (f), forming a spacer on ~~a sidewall~~ peripheral sidewalls of said single crystal island.

9. (Original) The method of claim 1, wherein said one or more devices are independently selected from the group consisting of NFETS, PFETs, bipolar transistors, resistors and capacitors.

10. (Original) The method of claim 1, wherein step (d) further includes interconnecting said one or more devices to form an integrated circuit in said second-single crystal layer.

11. (Original) The method of claim 10, wherein said integrated circuit is a radio frequency identification circuit.

12. (Original) The method of claim 1, wherein said trench comprises one or more intersecting trenches.

13. (Currently Amended) A method, comprising:

(a) providing a single-crystal substrate;

(b) forming a buried single-crystal layer in said substrate;

(c) forming one or more devices in said a layer of said single-crystal substrate above said buried single-crystal layer;

(d) forming a trench surrounding said one or more devices in a region of said layer of said single-crystal substrate above said buried single-crystal layer to form a single-crystal island containing said one or more devices, said buried single-crystal layer exposed in a bottom of said trench; and

[[(f)]] (e) removing said buried single-crystal layer in order to separate said single-crystal island from said substrate.

14. (Currently Amended) The method of claim 13, wherein step (b) includes performing an ion implantation of Ge or As or C followed by performing a heat treatment.

15-20 (Canceled)

21. (New) The method of claim 13, wherein said substrate comprises silicon.
22. (New) The method of claim 13, wherein said first single-crystal layer comprises Si_xGe_y , Si_xC_y or Si_xAs_y and said second single-crystal layer comprises silicon
23. (New) The method of claim 13, wherein said one or more devices are independently selected from the group consisting of NFETs, PFETs, bipolar transistors, resistors and capacitors.
24. (New) The method of claim 13, wherein step (d) further includes interconnecting said one or more devices to form an integrated circuit in said second-single crystal layer.
25. (New) The method of claim 24, wherein said integrated circuit is a radio frequency identification circuit.
26. (New) The method of claim 13, wherein said trench comprises one or more intersecting trenches.
27. (New) A method, comprising:
- (a) providing a substrate;
 - (b) forming a first single-crystal layer on a top surface of said substrate;
 - (c) forming a second single-crystal layer on a top surface of said first single-crystal layer;
 - (d) forming one or more devices in said second single-crystal layer;

(e) forming a trench in said second-single crystal layer to form a single-crystal island containing said one or more devices, said first single-crystal layer exposed in a bottom of said trench; and

(f) removing said first single-crystal layer in order to separate said single-crystal island from said substrate.